

[54] **TA-CONTAINING AMORPHOUS ALLOY LAYERS AND PROCESS FOR PRODUCING THE SAME**

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[57] **ABSTRACT**

An amorphous alloy layer comprised of Ta and another element selected from the group consisting of Ni, Co and N is formed by vapor deposition of the select elements onto a low temperature (below about -90° C.) substrate, such as glass. The resultant amorphous alloy layers are useful in thin film technology and are generally stable at room temperatures and up to about 300° C. while exhibiting a specific electrical resistance generally ranging from about 130 to 900 μΩ·cm and exhibit a relatively low temperature coefficient for such resistance, generally ranging from about -950 to +500 ppm/° K.

2 Claims, 1 Drawing Figure

